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1, 2, 4 and 8-Channel Very Low Capacitance ESD Protectors

Features

- 1,2,4 and 8 channels of ESD protection
- Very low loading capacitance (1.0pF typical)
- <u>+</u>6 kV ESD protection per channel (IEC 61000-4-2 standard)
- Available in SOT23, SOT143, SC70 and MSOP packages
- Lead-free versions available

Applications

- USB2.0 ports at 480Mbps
- IEEE1394 Firewire ports at 400Mbps
- Gigabit Ethernet ports
- Flat panel display interfaces
- Wireless antennas
- General purpose high-speed data line ESD protection

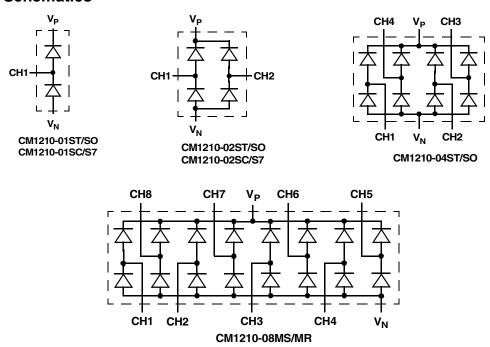
Product Description

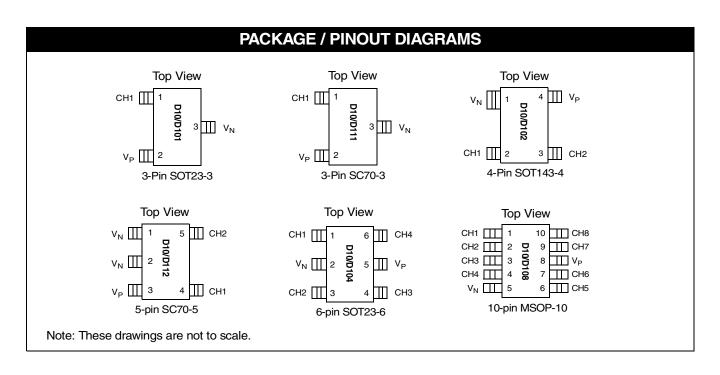
The CM1210 family of diode arrays has been designed to provide ESD protection for electronic components or sub-systems requiring minimal capacitive loading. These devices are ideal for protecting systems with high data and clock rates or for circuits requiring low capacitive loading. Each ESD channel consists of a pair of diodes which will steer the ESD current pulse to either the positive (V_P) or negative (V_N) supply rail. The CM1210 will protect against ESD pulses up to \pm 6KV per the IEC 61000-4-2 standard.

This device is particularly well-suited for systems using high-speed port implementations such as USB2.0, IEEE1394 (Firewire®, i.LinkTM), Gigabit Ethernet and corresponding ports in removable storage, digital camcorders, DVD-RW drives and other applications where extremely low loading capacitance with ESD protection are required in a small package footprint.

The CM1210 family of devices is optionally available with lead-free finishing.

Electrical Schematics





	SOT23-3 & SC70-3 PACKAGE PIN DESCRIPTIONS				
PIN	NAME	TYPE	DESCRIPTION		
1	CH1	I/O	ESD Channel		
2	V _P	PWR	Positive voltage supply rail		
3	V _N	GND	Negative voltage supply rail		
S	C70-5	PACKAG	E PIN DESCRIPTIONS		
PIN	NAME	TYPE	DESCRIPTION		
1	V _N	GND	Negative voltage supply rail		
2	V _N	GND	Negative voltage supply rail		
3	V _P	PWR	Positive voltage supply rail		
4	CH1	I/O	ESD Channel		
5	CH2	I/O	ESD Channel		
SC	DT23-6	PACKAG	GE PIN DESCRIPTIONS		
PIN	NAME	TYPE	DESCRIPTION		
1	CH1	I/O	ESD Channel		
2	V _N	GND	Negative voltage supply rail		
3	CH2	I/O	ESD Channel		
4	СНЗ	I/O	ESD Channel		
5	V _P	PWR	Positive voltage supply rail		
6	CH4	I/O	ESD Channel		

SO	T143-4	PACKA	GE PIN DESCRIPTIONS
PIN	NAME	TYPE	DESCRIPTION
1	V _N	GND	Negative voltage supply rail
2	CH1	I/O	ESD Channel
3	CH2	I/O	ESD Channel
4	V _P	PWR	Positive voltage supply rail
MS	SOP-10	PACKA	GE PIN DESCRIPTIONS
PIN	NAME	TYPE	DESCRIPTION
1	CH1	I/O	ESD Channel
2	CH2	I/O	ESD Channel
3	СНЗ	I/O	ESD Channel
4	CH4	I/O	ESD Channel
5	V _N	GND	Negative voltage supply rail
6	CH5	I/O	ESD Channel
7	CH6	I/O	ESD Channel
8	V _P	PWR	Positive voltage supply rail
9	CH7	I/O	ESD Channel
10	CH8	I/O	ESD Channel

Ordering Information

PART NUMBERING INFORMATION					
		Standa	rd Finish	Lead-fre	ee Finish
Pins	Package	Ordering Part Number ¹	Part Marking	Ordering Part Number ¹	Part Marking
3	SOT23-3	CM1210-01ST	D10	CM1210-01SO	D101
3	SC70-3	CM1210-01SC	D10	CM1210-01S7	D111
4	SOT143-4	CM1210-02ST	D10	CM1210-02SO	D102
5	SC70-5	CM1210-02SC	D10	CM1210-02S7	D112
6	SOT23-6	CM1210-04ST	D10	CM1210-04SO	D104
10	MSOP-10	CM1210-08MS	D10	CM1210-08MR	D108

Note 1: Parts are shipped in Tape & Reel form unless otherwise specified.

Specifications

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	RATING	UNITS			
Supply Voltage (V _P - V _N)	8.0	V			
Diode Forward DC Current (Note 1)	8	mA			
Operating Temperature Range	-40 to +85	°C			
Storage Temperature Range	-65 to +150	°C			
DC Voltage at any channel input	(V _N - 0.5) to (V _P + 0.5)	V			
Package Power Rating SOT23-3 Package (CM1210-01ST/SO) SC70-3 Package (CM1210-01SC/S7) SOT143 Package (CM1210-02ST/SO) SC70-5 Package (CM1210-02SC/S7) SOT23-6 Package (CM1210-04ST/SO) MSOP10 Package (CM1210-08MS/MR)	225 200 225 200 225 400	mW mW mW mW mW			

Note 1: Only one diode conducting at a time.

STANDARD OPERATING CONDITIONS					
PARAMETER	RATING	UNITS			
Operating Temperature Range	-40 to +85	°C			
Operating Supply Voltage (V _P - V _N)	0 to 5.5	V			

	ELECTRICAL OPERATING CHARACTERISTICS (SEE NOTE 1)						
SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT S	
l _P	Supply Current	(V _P -V _N)=3.3V			8.0	μA	
V _F	Diode Forward Voltage Top Diode Bottom Diode	I _F = 8mA	0.60 0.60	0.80 0.80	0.95 0.95	V V	
I _{LEAK}	Channel Leakage Current			<u>+</u> 0.1	<u>+</u> 1.0	μA	
C _{IN}	Channel Input Capacitance	At 1 MHz, V _P =3.3V, V _N =0V, V _{IN} =1.65V; Note 2 applies		1.0	1.3	pF	
V _{ESD}	ESD Protection Peak Discharge Voltage at any channel input, in system a) Contact discharge per IEC 61000-4-2 standard	Notes 2,3 and 5; T _A =25°C	<u>-</u> 6			kV	
V _{CL}	Channel Clamp Voltage CM1210-01ST, CM1210-01SC, CM1210-02ST, CM1210-02SC Positive Transients Negative Transients	At 8kV ESD HBM; Notes 2 & 4			V _P + 10.0 V _N - 10.0	V V	
	Channel Clamp Voltage CM1210-04ST, CM1210-08MS Positive Transients Negative Transients	At 8kV ESD HBM; Notes 2 & 4			V _P + 13.0 V _N - 13.0	V V	

Note 1: All parameters specified at $T_A = -40^{\circ}C$ to $+85^{\circ}C$ unless otherwise noted.

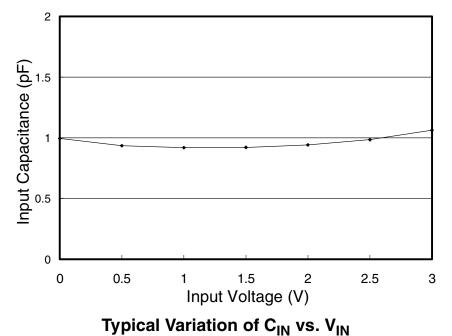
Note 2: These parameters guaranteed by design and characterization.

Note 3: From I/O pins to V_P or V_N only. V_P bypassed to V_N with a 0.22µF ceramic capacitor (see Application Information for more details).

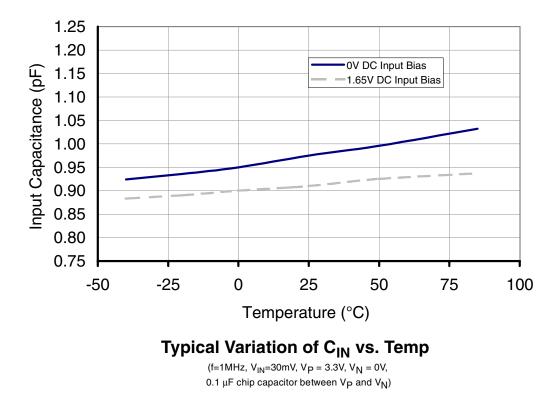
- Note 4: Human Body Model per MIL-STD-883, Method 3015, C_{Discharge} = 100pF, R_{Discharge} = 1.5KQ, V_P = 3.3V, V_N grounded.
- Note 5: Standard IEC 61000-4-2 with C_{Discharge} = 150pF, R_{Discharge} = 330Ω V_P = 3.3V, V_N grounded.

Performance Information

Input Channel Capacitance Performance Curves



(f=1MHz, V_P = 3.3V, V_N = 0V, 0.1 μF chip capacitor between V_P and V_N 25°C)



Performance Information (Cont'd)

Typical Filter Performance (nominal conditions unless specified otherwise, 50 Ohm Environment)

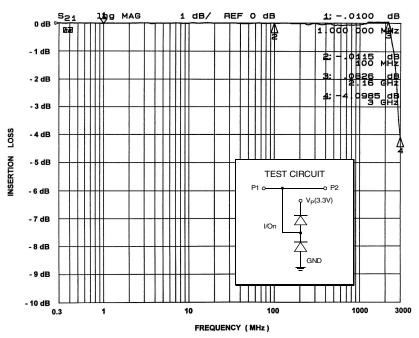


Figure 1. Insertion Loss (S21) VS. Frequency (0V DC Bias, V_P=3.3V)

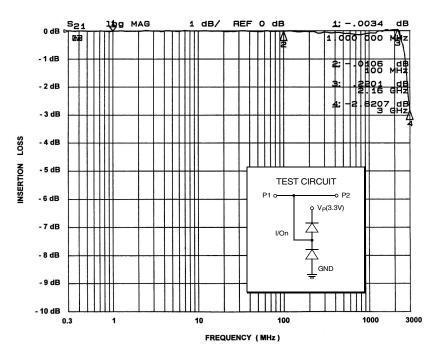


Figure 2. Insertion Loss (S21) VS. Frequency (2.5V DC Bias, V_P=3.3V)

Application Information

Design Considerations

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/ Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Figure 3, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to the power supply is represented by L_1 and L_2 . The voltage V_{CL} on the line being protected is:

 $V_{CL} = Fwd \text{ voltage drop of } D_1 + V_{SUPPLY} + L_1 \text{ x } d(I_{ESD}) / dt$ $+ L_2 \text{ x } d(I_{ESD}) / dt$

where I_{ESD} is the ESD current pulse, and $\mathsf{V}_{\text{SUPPLY}}$ is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000-4-2 standard results in a current pulse that rises from zero to 30 Amps in 1ns. Here $d(I_{ESD})/dt$ can be approximated by $\Delta I_{ESD}/\Delta t$, or $30/(1 \times 10^{-9})$. So just 910nH of series inductance (L₁ and L₂ combined) will lead to a 300V increment in V_{CI}!

Similarly for negative ESD pulses, parasitic series inductance from the V_N pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

Another consideration is the output impedance of the power supply for fast transient currents. Most power supplies exhibit a much higher output impedance to fast transient current spikes. In the V_{CL} equation above, the V_{SUPPLY} term, in reality, is given by (V_{DC} + I_{ESD} x R_{OUT}), where V_{DC} and R_{OUT} are the nominal supply DC output voltage and effective output impedance of the power supply respectively. As an example,

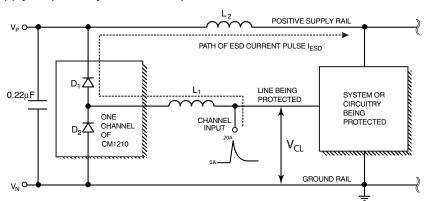
a R_{OUT} of 1 ohm would result in a 10V increment in V_{CL} for a peak I_{ESD} of 10A.

If the inductances and resistance described above are close to zero, the rail-clamp ESD protection diodes will do a good job of protection. However, since this is not possible in practical situations, a bypass capacitor must be used to absorb the very high frequency ESD energy. So for any brand of rail-clamp ESD protection diodes, a bypass capacitor should be connected between the V_{P} pin of the diodes and the ground plane (V_N pin of the diodes) as shown in the Application Circuit diagram below. A value of 0.22µF is adequate. Ceramic chip capacitors mounted with short printed circuit board traces are good choices for this application. Electrolytic capacitors should be avoided as they have poor high frequency characteristics. For extra protection, connect a zener diode in parallel with the bypass capacitor to mitigate the effects of the parasitic series inductance inherent in the capacitor. The breakdown voltage of the zener diode should be slightly higher than the maximum supply voltage.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the V_P pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

Additional Information

See also California Micro Devices Application Notes AP209, "Design Considerations for ESD Protection" and APxxx, "ESD Protection for USB 2.0 Systems".





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CM1210

Mechanical Details

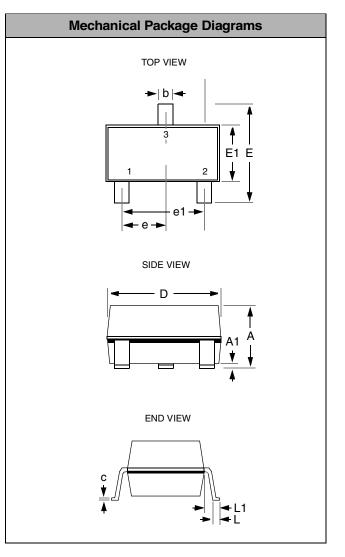
The CM1210 is available in SOT23-3, SC70-3, SC70-5, SOT23-6, SOT143-4 and MSOP-10 packages.The various package drawings are presented below.

SOT23-3 Mechanical Specifications

Dimensions for CM1210 devices packaged in 3-pin SOT23 packages are presented below.

For complete information on the SOT23-3 package, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS					
Package	SOT2	3-3 (JEDE0	C name is T	O-236)	
Pins			3		
Dimensions	Millir	neters	Inches		
Dimensions	Min	Max	Min	Мах	
А	0.89	1.12	0.0350	0.0441	
A1	0.01	0.10	0.0004	0.0039	
b	0.30	0.50	0.0118	0.0197	
с	0.08	0.20	0.0031	0.0079	
D	2.80	3.04	0.1102	0.1197	
E	2.10	2.64	0.0827	0.1039	
E1	1.20	1.40	0.0472	0.0551	
е	0.95	BSC	0.037	4 BSC	
e1	1.90	BSC	0.074	8 BSC	
L	0.40	0.60	0.0157	0.0236	
L1	0.54 REF 0.0213 REF				
# per tape and reel	3000 pieces				
C	ontrolling d	imension: n	nillimeters		



Package Dimensions for SOT23-3.

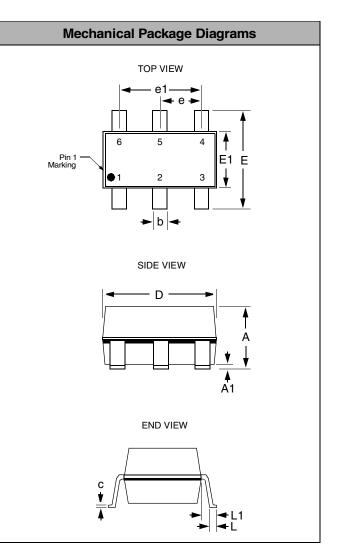
Mechanical Details (cont'd)

SOT23-6 Mechanical Specifications

CM1210 devices are packaged in 6-pin SOT23 packages. Dimensions are presented below.

For complete information on the SOT23-6 package, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS					
Package	SOT2	3-6 (JEDEC	name is M	O-178)	
Pins			6		
Dimensions	Millir	neters	Inc	hes	
Dimensions	Min	Max	Min	Мах	
A		1.45		0.0571	
A1	0.00	0.15	0.0000	0.0059	
b	0.30	0.50	0.0118	0.0197	
с	0.08	0.22	0.0031	0.0087	
D	2.75	3.05	0.1083	0.1201	
E	2.60	3.00	0.1024	0.1181	
E1	1.45	1.75	0.0571	0.0689	
е	0.95	BSC	0.037	4 BSC	
e1	1.90	BSC	0.074	8 BSC	
L	0.30	0.60	0.0118	0.0236	
L1	0.60 REF 0.0236 REF				
# per tape and reel	3000 pieces				
C	ontrolling d	imension: n	nillimeters		



Package Dimensions for SOT23-6.

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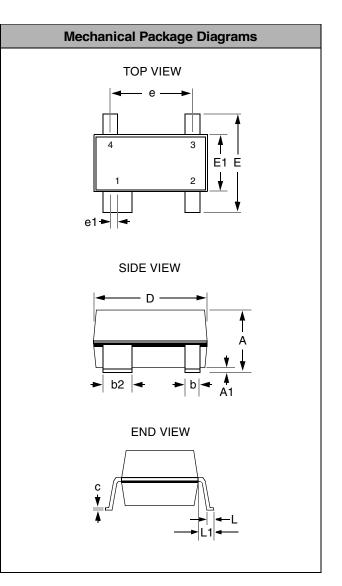
Mechanical Details (cont'd)

SOT143 Mechanical Specifications

Dimensions for CM1210 devices packaged in 4-pin SOT143 packages are presented below.

For complete information on the SOT143 package, see the California Micro Devices SOT143 Package Information document.

PACKAGE DIMENSIONS					
Package		SO	T143		
Pins			4		
Dimensions	Millir	neters	Inc	hes	
Dimensions	Min	Max	Min	Мах	
Α	0.80	1.22	0.031	0.048	
A1	0.05	0.15	0.002	0.006	
b	0.30	0.50	0.012	0.019	
b2	0.76	0.89	0.030	0.035	
с	0.08	0.20	0.003	0.008	
D	2.80	3.04	0.110	0.119	
E	2.10	2.64	0.082	0.103	
E1	1.20	1.40	0.047	0.055	
е	1.92	2 BSC	0.07	5 BSC	
e1	0.20) BSC	0.00	8 BSC	
L	0.4	0.6	0.016	0.024	
L1	0.54 REF 0.021 REF				
# per tape and reel	3000 pieces				
C	Controlling dimension: millimeters				



Package Dimensions for SOT143.

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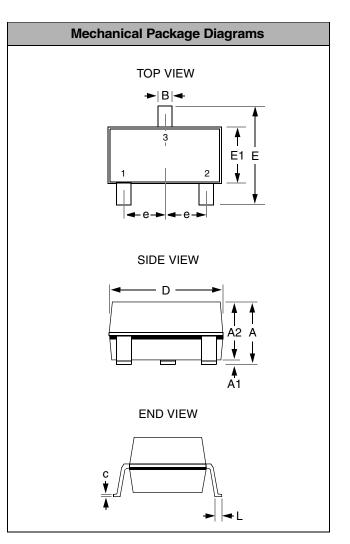
Mechanical Details (cont'd)

SC70-3 Mechanical Specifications

Dimensions for CM1210 devices packaged in 3-pin SC70 packages are presented below.

For complete information on the SC70-3 package, see the California Micro Devices SC70 Package Information document.

PACKAGE DIMENSIONS					
Package		70-3 MO-203 Issue A)			
Pins		3			
Dimensions	Millin	neters			
Dimensions	Min	Max			
Α	0.80	1.10			
A1	0.00	0.10			
A2	0.70	1.00			
В	0.15	0.30			
c	0.08	0.25			
D	1.85	2.25			
E1	1.15	1.35			
e	0.65 BSC				
E	2.00	2.40			
L	0.26	0.46			
# / tape and reel	3000	pieces			



Package Dimensions for SC70-3.

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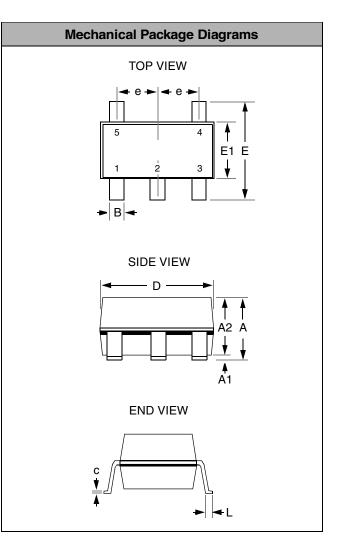
Mechanical Details (cont'd)

SC70-5 Mechanical Specifications:

Dimensions for CM1210 devices packaged in 5-pin SC70 packages are presented below.

For complete information on the SC70-5 package, see the California Micro Devices SC70 Package Information document.

PACKAGE DIMENSIONS					
Package		70-5 s MO-203 Issue A)			
Pins		5			
Dimensions	Milli	neters			
Dimensions	Min	Мах			
A	0.80	1.10			
A1	0.00	0.10			
A2	0.70	1.00			
В	0.15 0.30				
С	0.08	0.25			
D	1.85	2.25			
E1	1.15	1.35			
е	0.65 BSC				
E	2.00	2.40			
L	0.26	0.46			
# / tape and reel	3000 pieces				



Package Dimensions for SC70-5.

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Mechanical Details (cont'd)

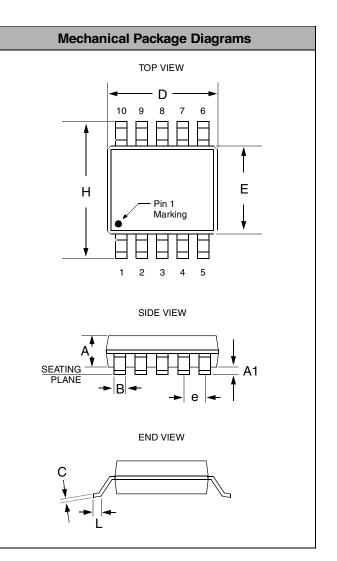
MSOP Mechanical Specifications

CM1210 devices are packaged in 10-pin MSOP packages. Dimensions are presented below.

For complete information on the MSOP-10 package, see the California Micro Devices MSOP Package Information document.

PACKAGE DIMENSIONS					
Package		MS	SOP		
Pins		-	10		
Dimensions	Millir	neters	Inc	hes	
Dimensions	Min	Мах	Min	Max	
Α	0.75	0.95	0.028	0.038	
A1	0.05	0.15	0.002	0.006	
В	0.18	0.40	0.006	0.016	
С	0	.18	0.0	007	
D	2.90	3.10	0.114	0.122	
E	2.90	3.10	0.114	0.122	
е	0.50	BSC	0.019	6 BSC	
н	4.76	5.00	0.187	0.197	
L	0.40	0.70	0.0137	0.029	
# per tube	80 pieces*				
# per tape and reel	4000				
	Controlling dimension: inches				

* This is an approximate number which may vary.



Package Dimensions for MSOP-10